Electrical Characteristics at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	BV_{DSS}	650	-	-	V
Drain-Source Leakage Current	V_{DS} =650 V, V_{GS} = 0 V	I_{DSS}	-	-	1	μA
Gate Leakage Current	V_{GS} = ± 30 V, V_{DS} = 0 V	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	$V_{GS(th)}$	2	-	4	V
Drain-source on-state resistance	V_{GS}=10V, I_D=15A	$R_{DS(ON)}$	-	120	130	mΩ
Input Capacitance	V_{GS}=0V V_{DS}=50V f=1.0MHz	C_{iss}	-	1950	-	pF
Output Capacitance		C_{oss}	-	245	-	
Reverse Transfer Capacitance		C_{rss}	-	29	-	
Turn-on Delay Time(Note2)	V_{DS} =300V I_D = 30 A R_G =25Ω	$t_{d(on)}$	-	30	-	ns
Rise Time(Note2)		T_r	-	45	-	
Turn-Off Delay Time(Note						

Ratings and Characteristic Curves

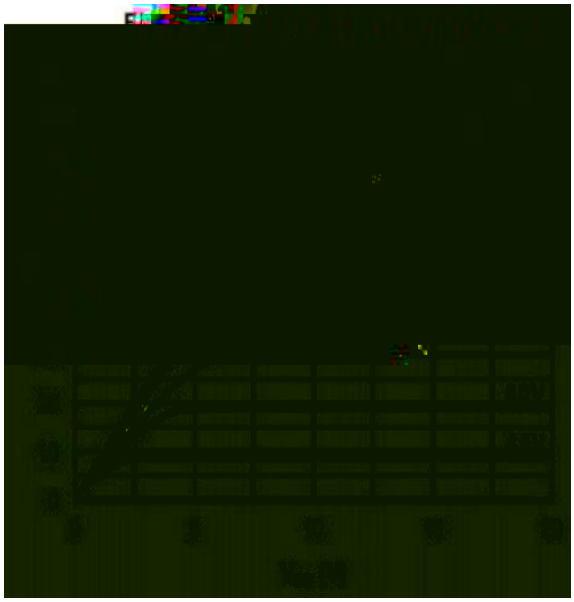


Figure2. Transfer Characteristics

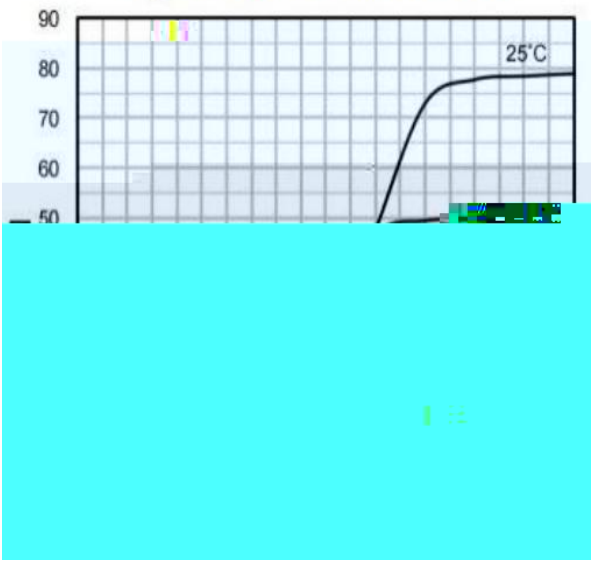


Figure 3. On-Resistance VS.Drain Current

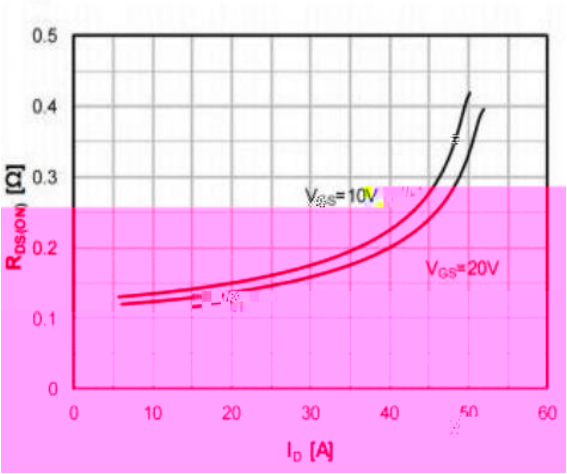




Figure 5. Gate Charge

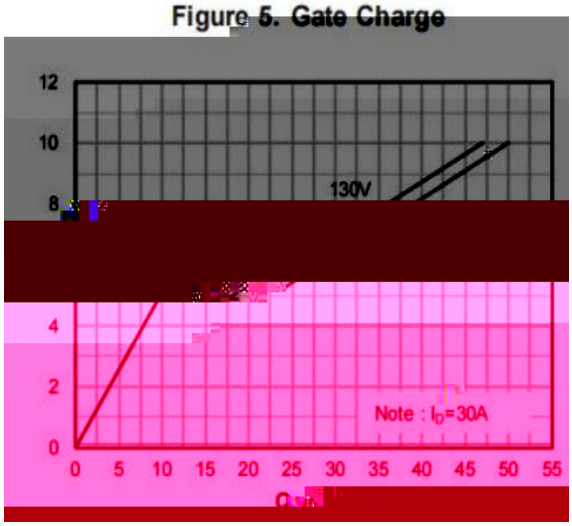
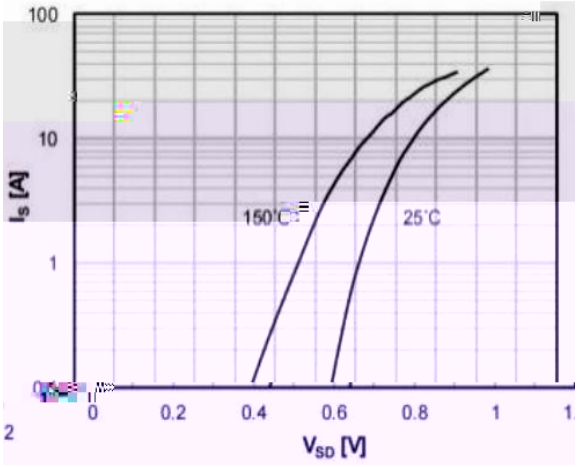
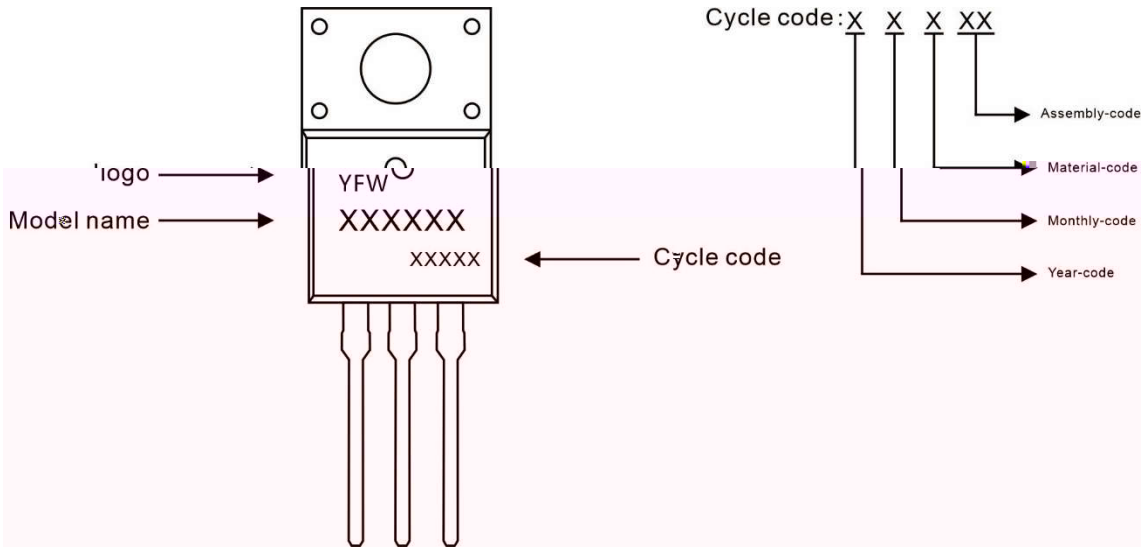
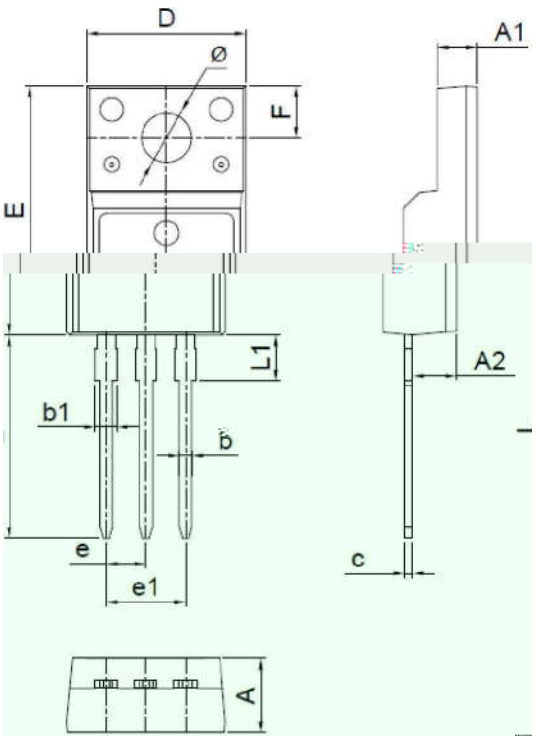


Figure 6.Body Diode Forward Voltage





	TO-220F	0.06oz(1.74g)	50pcs/tube	1000PCS/Box 5000PCS/Carton



A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.66	2.86	0.105	0.113
b	0.75	0.85	0.030	0.033
b1	1.24	1.44	0.049	0.057
c	0.40	0.60	0.016	0.024
D	10.00	10.32	0.394	0.406
E	15.75	16.05	0.620	0.632
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	3.10	3.5	0.122	0.138
L	13.50	13.90	0.531	0.547
L1	2.90	3.30	0.114	0.130
Φ	3.10	3.30	0.122	0.130